

Can zinc oxide thin films be used in a-Si solar cell?

The QE curves of the solar cells with Al or ZnO/Al back contacts. 4. Conclusions In summary, large area zinc oxide thin films have been prepared and applied in the a-Si solar cell by MOCVD technique using DEZn and H<sub>2</sub>O, with B<sub>2</sub>H<sub>6</sub> as doping gas.

How are boron-doped zinc oxide films grown?

Boron-doped zinc oxide (ZnO:B) films were grown by metal organic chemical vapor deposition using diethylzinc (DEZn), and H<sub>2</sub>O as reactant gases and diborane (B<sub>2</sub>H<sub>6</sub>) as an n-type dopant gas. The structural, electrical and optical properties of ZnO films doped at different B<sub>2</sub>H<sub>6</sub> flow rates were investigated.

How conductive boron-doped zinc oxide films are deposited?

Herein, conductive boron-doped zinc oxide (ZnO:B) films are deposited by atomic layer deposition (ALD) process and investigated as electron-selective contacts, in combination with a thin SiO<sub>x</sub> passivating interlayer. This combination demonstrates a relative low contact resistivity of  $2 \text{ m}^2 \text{ cm}^{-2}$  and improved passivation quality.

How does boron doping affect the conductivity of ZnO film?

The conductivity of the ZnO:B film improves significantly when the boron doping ratio is increased to 10:1, achieving a best resistivity of about  $3.0 \text{ m}^2 \text{ cm}^{-2}$  (compared with pristine ZnO film with resistivity of about  $40.0 \text{ m}^2 \text{ cm}^{-2}$ ).

What characterized the effective minority carrier lifetimes of solar cells?

The effective minority carrier lifetimes of samples were characterized by photoconductance decay (Sinton WCT 120). Solar cells were demonstrated using a phosphorus-doped n-type c-Si wafer, with a full-area p<sup>+</sup> and local heavily doped p<sup>++</sup> emitter on the front side.

Can crystalline silicon (Si) solar cells be used in photovoltaic industry?

Combining electron- and hole-selective materials in one crystalline silicon (Si) solar cell, thereby avoiding any dopants, is not considered for application to photovoltaic industry until only comparable efficiency and stable performance are achievable.

ZnO has recently been intensively investigated as a candidate material for sustainable energy applications. ZnO is used as the active layer to create p-n or n-n hetero-junction and also as antireflection coating in hetero-junction solar cells (Fox and Bertsch, 2002). ZnO has the potential to replace TiO<sub>2</sub> in dye sensitized solar cells (DSSC) due to its ...

This electron-selective passivating contact structure, prepared via low-temperature, simplified, and the

compositionally controlled ALD process, offers a promising pathway for the development of high-efficiency and low-cost c-Si solar cells.

We report on the photovoltaic properties of inverted polymer solar cells (IPSCs) where the transparent indium tin oxide (ITO) electrode was modified by a ZnO layer using metal organic chemical vapor deposition (MOCVD). The intrinsic ZnO (i-ZnO) layers were deposited with varying thicknesses from 0 to 1500 nm. The work function and ...

The exploration of wide-bandgap metal compound films with excellent passivation and contact properties on crystalline silicon (c-Si) surface, as alternatives to traditional-doped Si thin films,...

Solar cells were demonstrated using a phosphorus-doped n-type c-Si wafer, with a full-area p + and local heavily doped p ++ emitter on the front side. Al<sub>2</sub>O<sub>3</sub> (20 nm)/SiN<sub>x</sub> (55 nm) stacks were used as passivating and antireflection layer.

Recently, there have been lots of studies characterizing inverted solar cells that use ITO/ZnO transparent electrodes. In these studies, many methods have been employed for producing the ZnO layers, including solution processed sol-gel [17], [18], nanoparticles [19], [20], and sputtering [21]. Furthermore, different nanostructures, such as ZnO nanorods [16], [22], ...

enhancement of c-Si solar cell efficiency. Herein, conductive boron-doped zinc oxide (ZnO:B) films are deposited by atomic layer deposition (ALD) process and investigated as electron-selective contacts, in combination with a thin SiO<sub>x</sub> passivating interlayer. This combination demonstrates a relative low contact

enhancement of c-Si solar cell efficiency. Herein, conductive boron-doped zinc oxide (ZnO:B) films are deposited by atomic layer deposition (ALD) process and investigated ...

Textured surface boron-doped zinc oxide (BZO) thin films were fabricated by metal organic chemical vapor deposition as transparent conductive oxide (TCO) for solar cells. The surface microstructure was characterized by X ...

However, the front emitter structure of TOPCon solar cell is the same as in the traditional PERT solar cell with a thermally boron (B) diffused emitter with BBr<sub>3</sub> or BCl<sub>3</sub> as the B source, which not only becomes one of the efficiency limitations, but also has some disadvantages from solar cell manufacturing point of view. First, using BBr<sub>3</sub> or BCl<sub>3</sub> as the ...

Indium consumption is the roadblock for terawatt-scale silicon heterojunction (SHJ) solar cells. Here, we report that M6 wafer scale SHJ cells reached an efficiency of 24.94% using room temperature DC sputtering deposited ZnO:Al (AZO) transparent electrode. Compared with indium tin oxide (ITO) standard cells, interfacial contact and smaller bandgap are ...

Boron-doped ZnO:B (BZO) films with various doping levels have been prepared on large-area substrates by low pressured chemical vapor deposition technique. The influence of doping amount on electrical and optical properties of BZO films has been investigated. It is found that ZnO phase synthesis is hardly affected when the doping gas flow varies from 25 to 100 ...

This electron-selective passivating contact structure, prepared via low-temperature, simplified, and the compositionally controlled ALD process, offers a promising ...

With the increase in boron concentration, bandgap and resistivity of the ZnO: B varied from 2.96 to 3.72 eV and 120  $\Omega$ -cm to 58  $\Omega$ -cm, respectively. Based on the results obtained, we believe that ZnO: B is suitable as a window layer for solar light trapping in the fabrication of a photovoltaic cell.

Zinc oxide (ZnO) films play an important role in improving the conversion efficiency of Si-based thin film solar cells as the transparent conductive front electrodes and ...

Textured boron-doped zinc oxide (ZnO:B) films, suitable as transparent and conductive layers in thin film silicon-based solar cells, have been obtained by low-pressure metalorganic chemical vapour ...

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